

Semiconductors-Discretes

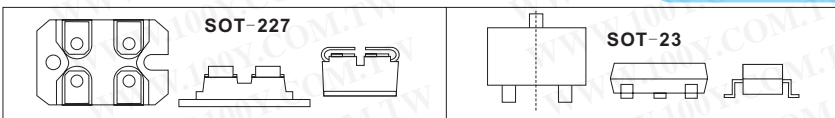
Other Series Power MOSFET

Detailed product specifications are available on: us.100y.com.tw

| Part No. | Product No. | Manufacturer | Description | Pin/Package | Id(max.) A | Rds(on)(max.) Ω | Pd(max.) W | Vdss(max.) V | N/P Ch. |
|----------|-------------|--------------|--|-------------------|------------|-----------------|------------|--------------|---------|
| 33035 | VN0610L | VISHAY | N-Channel Enhancement-Mode MOS Transistors | 3P/TO-92 | 0.27A | 5Ω | 0.8W | 60V | N |
| 35669 | VN10LM | | N-Channel Enhancement-Mode MOS Transistors | 3P/TO-237 | 0.32A | 5 | 1W | 60 | N |
| 33029 | VN10LP | ZETEX | N-channel enhancement mode vertical dmos fet | 3P/TO92 | 270mA | 5Ω | 625mW | 60V | N |
| 33023 | VN2222LL | VISHAY | N-Channel 60-V (D-S) MOSFETs | 3P/TO-92 | | 7.5Ω | 0.8W | 60V | N |
| 33015 | VN2410L | VISHAY | N-Channel Enhancement-Mode | 3P/TO-92 | 1.0A | 10Ω | | 240V | N |
| 27086 | VN50300T | VISHAY | N-Channel 500-V (D-S) MOSFETs | 3P/TO-236(SOT-23) | 0.022 | 240 | 0.35W | 500V | N |
| 33042 | VN88AFD | VISHAY | N-Channel 80-V and 90-V (D-S) MOSFETS | 3P/TO-220SD | 1.29A | 4Ω | 15W | 80V | N |
| 33045 | VND5N07 | ST(SGS) | Fully autoproctected power mosfet | DPAK(29) | 4.0A | 0.2Ω | 60W | 80V | |
| 33101 | VNP10N06 | ST(SGS) | Fully autoproctected power mosfet | TO-220 | 15A | 300mΩ | 42W | 70V | |
| 33104 | VNP10N07 | ST(SGS) | Fully autoproctected power mosfet | TO-220 | 14A | 100mΩ | 50W | 80V | |
| 33107 | VNP20N07 | ST(SGS) | Fully autoproctected power mosfet | TO-220 | 28A | 50mΩ | 83W | 80V | |
| 33110 | VNP28N04 | ST(SGS) | Fully autoproctected power mosfet | TO-220 | 49A | 35mΩ | 83W | 42V | |
| 33112 | VNP35N07 | ST(SGS) | Fully autoproctected power mosfet | TO-220 | 45A | 28mΩ | 125W | 80V | |
| 33116 | VNP49N04 | ST(SGS) | Fully autoproctected power mosfet | TO-220 | 68A | 20mΩ | 125W | 48V | |
| 33099 | VNP5N07 | ST(SGS) | Fully autoproctected power mosfet | TO-220 | 7A | 200mΩ | 31W | 80V | |
| 33117 | VNW100N04 | ST(SGS) | Fully autoproctected power mosfet | 3P/TO-247 | 140A | 12mΩ | 208W | 48V | |
| 32675 | VP0610L | VISHAY | P-Channel 60-V (D-S) MOSFET | SOT-23 | 0.18A | -10V | 0.8V | -60V | P Ch. |
| 32677 | VQ1000J | VISHAY | N-Channel 60-V (D-S) MOSFET | Dual-In-Line | 0.225A | 10V | 1.3W | 60V | N |
| 32451 | ZVN2106A | ZETEX | N-channel enhancement | 3P/TO-92 | 450mA | 2Ω | 700mW | 60V | TO-92 |
| 32449 | ZVN2110A | ZETEX | N-channel enhancement | 3P/TO-92 | 320mA | 4Ω | 700mW | 100V | TO-92 |
| 32446 | ZVN3306A | ZETEX | N-channel enhancement | 3P/TO-92 | 270mA | 5Ω | 625mW | 60V | TO-92 |
| 32442 | ZVN4206A | ZETEX | N-channel enhancement | 3P/TO-92 | 600mA | 1Ω | 0.7W | 60V | TO-92 |
| 40616 | ZXM64N02X | ZETEX | 20V N-channel enhancement mode mosfet | MSOP8 | 5.4A | 0.040 | 1.1W | 20V | N-Ch. |

Power MOSFET Modules

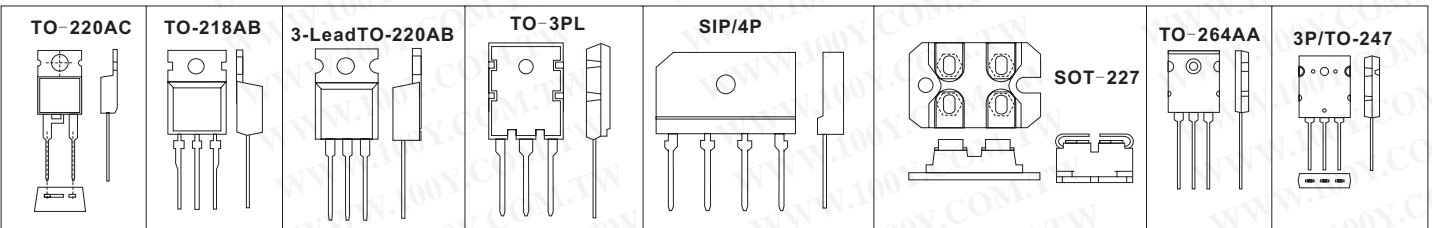
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| Part No. | Product No. | Manufacturer | Description | Id(Cont..) A | Rds(on)Ω | Pd(max.) W | Vdss(max.) V | Package |
|----------|-------------|--------------|---------------------|--------------|----------|------------|--------------|---------|
| 16557 | APT10025JVR | APT | Power MOSFET Module | 34A | 0.25Ω | 700W | 1000V | SOT-227 |
| 17626 | APT10050JN | APT | Power MOSFET Module | 20.5A | 0.50Ω | 520W | 1000V | SOT-227 |
| 42201 | MMBF170LT3 | ON-Semi. | Power MOSFET | 0.5A | | | 60V | SOT-23 |
| 42203 | MMBF170LT3G | ON-Semi. | Power MOSFET | 0.5A | | | 60V | SOT-23 |
| 42205 | MMBF5457LT1 | ON-Semi. | Small Signal JFET | 5mA | | | 25V | SOT23 |
| 21941 | TE53N50E | MOTOROLA | Power MOSFET Module | 53A | | 400W | 500V | |

IGBT Discretes Modules

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| Part No. | Product No. | Manufacturer | Description | Vces | Ic(A) | Pd(max)W | Package |
|----------|-------------|--------------|---|-------|----------|----------|-----------------|
| 35401 | 10ETF12 | IR | FAST SOFT RECOVERY RECTIFIER DIODE | 1200V | 10A | 12KW | TO-220AC |
| 28939 | BUP302 | SIEMENS | IGBT | 1000V | 12A | 125W | TO-218AB |
| 28940 | BUP303 | SIEMENS | IGBT | 1000V | 23A | 200W | TO-218AB |
| 28937 | BUP304 | SIEMENS | IGBT | 1000V | 35A | 310W | TO-218AB |
| 17918 | BUP307 | | IGBT | 1200V | 35A | 310W | TO-218AB |
| 28938 | BUP313 | SIEMENS | IGBT | 1200V | 32A | 200W | TO-218AB |
| 20239 | BUP314 | SIEMENS | IGBT | 1200V | 52A | 300W | TO-3P(TO-218AB) |
| 28943 | BUP400 | SIEMENS | IGBT | 600V | 22A | 100W | TO-220AB |
| 39314 | CT60AM-18F | RENESAS | INSULATED GATE BIPOLAR TRANSISTOR | 900V | 60A | 180W | TO-3PL |
| 39687 | D10XB60 | | Bridge Diode | 800V | 10A | 26w | SIP/4P |
| 33152 | GA200SA60S | IR | Insulated gate bipolar transistor | 600V | 200A max | 630W | SOT-227 |
| 33151 | GA200SA60U | IR | Insulated gate bipolar transistor | 600V | 200A max | 630W | SOT-227 |
| 33205 | GT15Q101 | TOSHIBA | N channel igbt (high power switching, motor control applications) | 1200V | 15.0A | 150.0W | TO3 |
| 10245 | GT60M-301 | TOSHIBA | IGBT | 900V | 60A | | 3P/TO-264 |

